

KM89528NFMA-A

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| 1. Material | GaAlAs |
| 2. Electrode | N (cathode) side : Au
P (anode) side : Au |
| 3. Electrode pattern | Fig.1 |
| 4. Chip size | 0.265 mm × 0.265 mm × 0.210 mm (Fig.1) |
| 5. Emission area | 0.230mm X 0.230mm (Fig.1) |
| 6. Electro-Optical characteristics (Ta = 25°C) | |

Parameters	Symbol	Condition	Min	Typ	Max	Unit
Power	Po	IF=20mA	2.0	4.2	-	mW
Forward Voltage	VF	IF=20mA	-	1.33	1.39	V
Reverse Current	IR	VR=3V	-	-	10	uA
Peak Wavelength	λ_p	IF=20mA	885	895	905	nm
Spectral Radiation Bandwidth	$\Delta\lambda^{(*)}$	IF=20mA	-	50	-	nm

* (*) mark is reference data

* Power Measurement at Resonac Photonics.

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| 7. Recommended bonding method | Ultra-sonic method or a combination of ultra-sonic and thermo-compression methods. |
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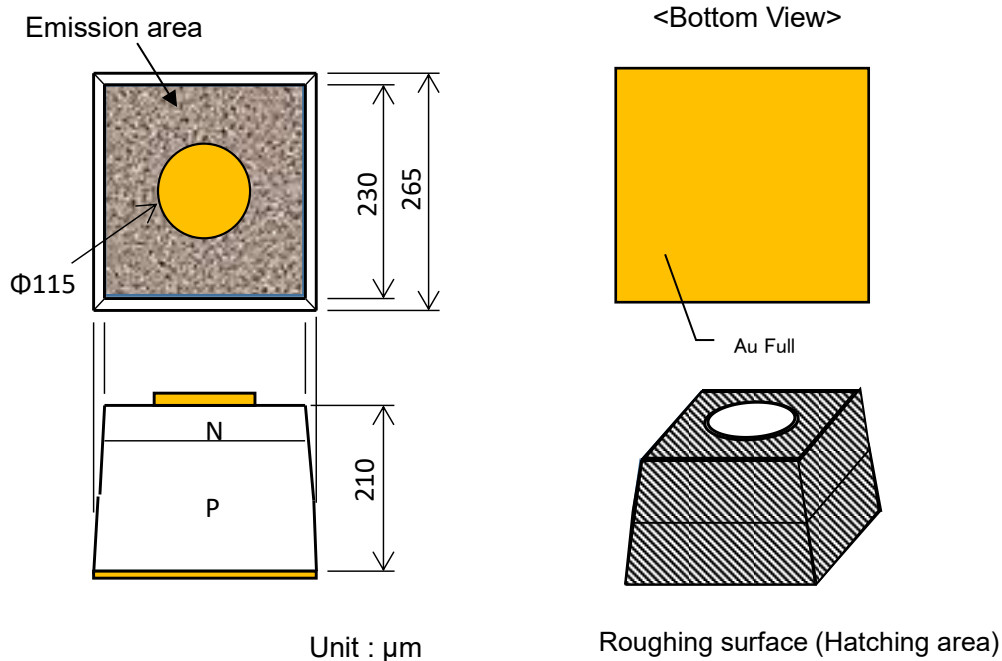


Fig.1 : Chip size and Emission area and Electrode pattern

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